CLAIMS

1. A method of forming a substrate opening, comprising:

forming a plurality of side-by-side openings in a substrate, immediately adjacent of the side-by-side openings having a wall there-between, at least some of the immediately adjacent side-by-side openings being formed in the substrate to different depths relative one another; and

removing all portions of said walls to form a larger opening having a non-vertical sidewall surface where the walls were removed in at least one straight-line vertical cross-section that passes through the non-vertical sidewall surface orthogonally to the removed walls.

2. The method of claim 1 wherein the forming comprises plasma etching.

3. The method of claim 2 comprising using only a single masking step to form the side-by-side openings having walls there-between.

4. The method of claim 1 wherein the plurality of side-by-side openings having walls there-between are individually sub-micron, and the larger opening is sub-micron.

5. The method of claim 1 wherein only some of immediately adjacent side-by-side openings having walls there-between are formed in the substrate to different depths relative one another.

6. The method of claim 1 wherein each immediately adjacent side-by-side opening having the walls there-between is of different depth in the substrate relative each other.

7. The method of claim 6 wherein all side-by-side openings having the walls there-between are of different depths relative one another.

8. The method of claim 1 wherein all of the substrate openings having the walls there-between are formed to be longitudinally elongated orthogonal to the straight-line vertical cross-section.

9. The method of claim 1 wherein at least one of the substrate openings having the walls there-between is formed to not be longitudinally elongated.

10. The method of claim 1 wherein the substrate openings having the walls there-between are formed to individually be of constant depth.

11. The method of claim 1 wherein the non-vertical sidewall surface is formed to be straight-linear along at least a majority of its length along the at least one straight-line vertical cross-section.

12. The method of claim 11 wherein the non-vertical sidewall surface is formed to be straight-linear along substantially all of its length along the at least one straight-line vertical cross-section.

13. The method of claim 1 wherein the non-vertical sidewall surface is formed to be curved along at least a majority of its length along the at least one straight-line vertical cross-section.

14. The method of claim 13 wherein the non-vertical sidewall surface is formed to be curved along substantially all of its length along the at least one straight-line vertical cross-section.

15. The method of claim 14 wherein the non-vertical sidewall surface is formed to be concave.

16. The method of claim 14 wherein the non-vertical sidewall surface is formed to be convex.

17. The method of claim 1 wherein the non-vertical sidewall surface is formed to have a combination of at least one straight-linear section and at least one curved section.

18. The method of claim 1 wherein the non-vertical sidewall surface is formed to have a combination of differently angled straight-linear sections.

19. The method of claim 1 wherein the larger opening is formed to comprise a vertical sidewall surface laterally opposite the non-vertical sidewall surface in the at least one straight-line vertical cross-section.

20. The method of claim 1 wherein the larger opening is formed to be devoid of any vertical sidewall surface laterally opposite the non-vertical sidewall surface in the at least one straight-line vertical cross-section.

21. The method of claim 1 wherein the larger opening is formed to be devoid of any vertical sidewall surface.

22. The method of claim 21 wherein the larger opening is formed to be “V”-shaped in the at least one straight-line vertical cross-section.

23. The method of claim 21 wherein the larger opening is formed to be “W”-shaped in the at least one straight-line vertical cross-section.

24. The method of claim 1 wherein the non-vertical sidewall surface extends to an elevationally outermost surface of the substrate after removal of any etch mask that might overlie the substrate.

25. The method of claim 1 wherein the larger opening is formed to comprise an elevationally outermost sidewall surface that is vertical and which joins with the non-vertical sidewall surface.

26. The method of claim 1 wherein the larger opening is formed to have a horizontal base surface orthogonal to the one straight-line vertical cross-section.

27. The method of claim 26 wherein the horizontal base surface extends along substantially all of the larger opening orthogonal to the one straight-line vertical cross-section.

28. The method of claim 1 wherein the larger opening is formed to have a non-horizontal base surface orthogonal to the one straight-line vertical cross-section.

29. The method of claim 28 wherein the non-horizontal base surface extends along substantially all of the larger opening orthogonal to the one straight-line vertical cross-section.

30. The method of claim 1 wherein the substrate openings having the walls there-between are formed to individually have multiple different outermost open dimensions, and the larger opening is formed to have a non-horizontal base surface orthogonal to the one straight-line vertical cross-section.

31. The method of claim 1 comprising forming the larger opening to be longitudinally elongated orthogonal the at least one straight-line cross-section.

32. The method of claim 1 wherein the forming comprises etching and the removing comprises etching, the forming and the removing comprising separate, different chemistry, time-spaced etching steps.

33. The method of claim 1 wherein the forming comprises etching and the removing comprises etching, the etching of the forming and the etching of the removing comprising a single continuous etching step from the forming through the removing.

34. A method of forming a substrate opening using an etch mask, the etch mask comprising a plurality of side-by-side openings, at least some immediately adjacent side-by-side openings having different minimum widths relative one another, the method comprising:

plasma etching a plurality of side-by-side openings into the substrate using the etch mask, immediately adjacent of the substrate openings having a wall there-between, the substrate openings etched though wider minimum-width openings in the etch mask being etched deeper into the substrate than the substrate openings etched through narrower minimum-width openings in the etch mask; and

removing all portions of said walls to form a larger opening having a non-vertical sidewall surface where the walls were removed in at least one straight-line vertical cross-section that passes through the non-vertical sidewall surface orthogonally to the removed walls.

35. The method of claim 34 wherein the etch mask is directly against the substrate.

36. The method of claim 34 wherein the etch mask is not directly against the substrate.

37. The method of claim 34 wherein the removing comprises etching.

38. The method of claim 37 wherein the etch mask is directly against the substrate, and the removing comprises:

continuing the plasma etching to remove walls that are laterally between the side-by-side openings in the etch mask and thereby elevationally exposing and etching away the walls that are laterally between the side-by-side substrate openings.